

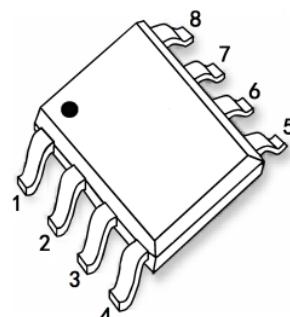
# KY4953C

-30V Dual P-Channel Mosfet

## FEATURES

- $R_{DS(ON)} \leq 87m\Omega$  ( 66m $\Omega$  Typ.) @ $V_{GS}=-10V$
- $R_{DS(ON)} \leq 130m\Omega$  ( 100m $\Omega$  Typ.) @ $V_{GS}=-4.5V$

## SOP-8

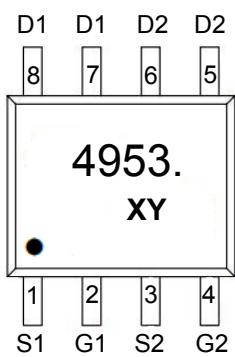


1: S1      3: S2      5: D2      7: D1  
2: G1      4: G2      6: D2      8: D1

## APPLICATIONS

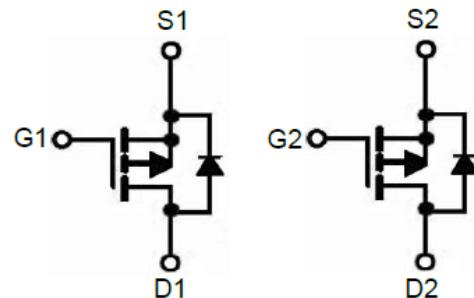
- PWM Applications
- Load Switch
- Power Management

## MARKING



XY: DC Code

## P-CHANNEL MOSFET



## MAXIMUM RATINGS Ta=25°C unless otherwise specified

Symbol	Parameter	Rating	Units
$V_{DSS}$	Drain-Source Voltage	-30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current	-3.8	A
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>	-12	A
$P_D$	Power Dissipation	2.0	W
$R_{\theta JA}$	Junction-to-Ambient	62.5	°C/W
$T_J$	Junction Temperature	150	°C
Tstg	Operating Junction and Storage Temperature Range	-55 to 150	°C

**KY4953C****ELECTRICAL CHARACTERISTICS Ta= 25°C unless otherwise specified**

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>OFF Characteristics</b>						
V <sub>DSS</sub>	Drain to Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30	--	--	V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	--	--	-1	μA
I <sub>GSS</sub>	Gate to Source Forward Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
<b>ON Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.8	-2	V
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance <sup>note2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	--	66	87	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	--	100	130	mΩ
<b>Dynamic Characteristics <sup>note3</sup></b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V f = 1.0MHz	--	320	--	pF
C <sub>oss</sub>	Output Capacitance		--	50	--	
C <sub>rss</sub>	Reverse Transfer Capacitance		--	35	--	
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =-3A, V <sub>DS</sub> =-15V V <sub>GS</sub> =-10V	--	9.0	--	nC
Q <sub>gs</sub>	Gate to Source Charge		--	1.5	--	
Q <sub>gd</sub>	Gate to Drain ("Miller") Charge		--	2.0	--	
<b>Switching Characteristics <sup>note3</sup></b>						
t <sub>d(on)</sub>	Turn-on Delay Time	I <sub>D</sub> =-1A, V <sub>DS</sub> =-15V V <sub>GS</sub> = -10V, R <sub>G</sub> =6Ω	--	5	--	ns
t <sub>r</sub>	Rise Time		--	11	--	
t <sub>d(off)</sub>	Turn-Off Delay Time		--	12	--	
t <sub>f</sub>	Fall Time		--	7	--	
<b>Source-Drain Diode Characteristics</b>						
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-3A, V <sub>GS</sub> =0V T <sub>J</sub> =25°C	--	--	-1.2	V

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2 . Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

3 . Guaranteed by design, not subject to production testing

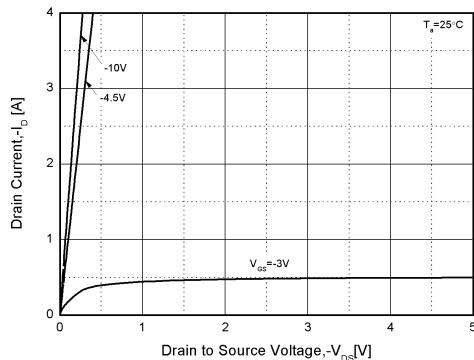
**TYPICAL PERFORMANCE CHARACTERISTICS**


Figure 1. Output Characteristics

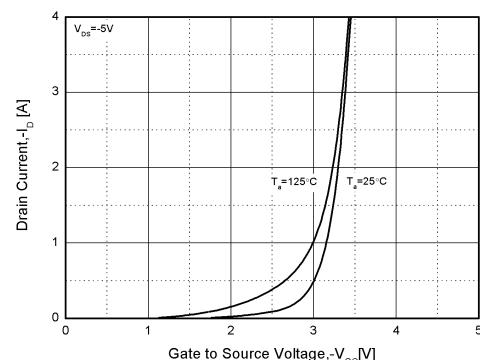


Figure 2. Transfer Characteristics

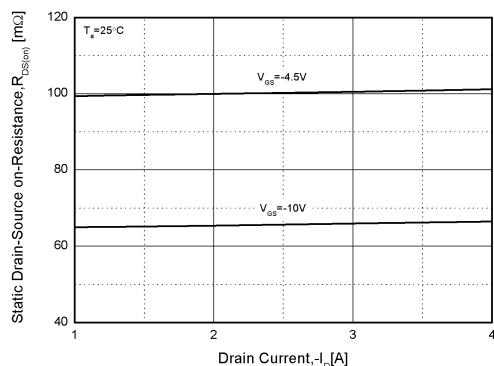


Figure 3. Rdson-Drain Current

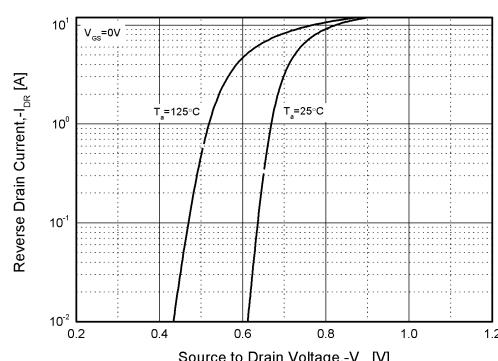


Figure 4. Typical Source-Drain Diode Forward Voltage

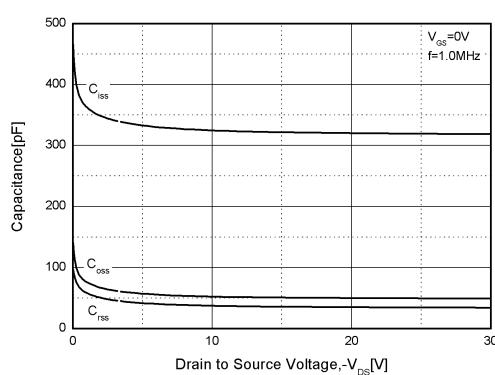


Figure 5. Capacitance Characteristics

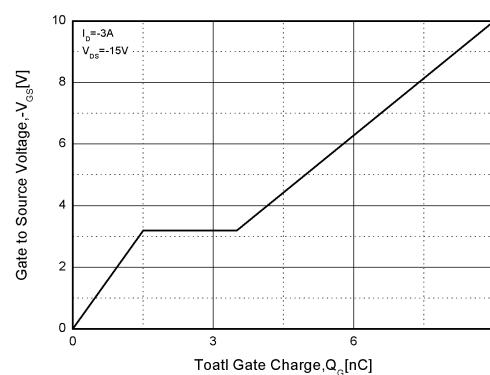


Figure 6. Gate Charge

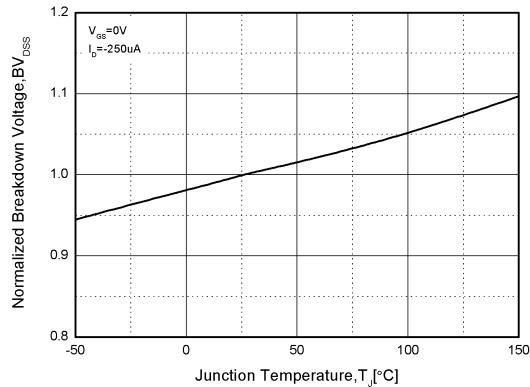
**TYPICAL PERFORMANCE CHARACTERISTICS (cont.)**


Figure7. Normalized Breakdown Voltage vs. Temperature

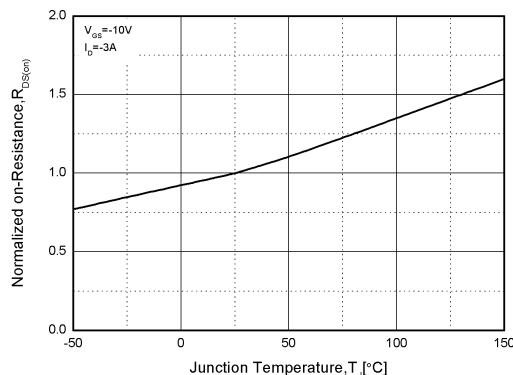


Figure8. Normalized on Resistance vs. Temperature

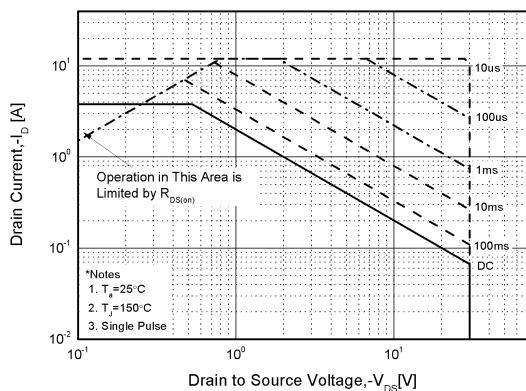


Figure9. Safe Operation Area

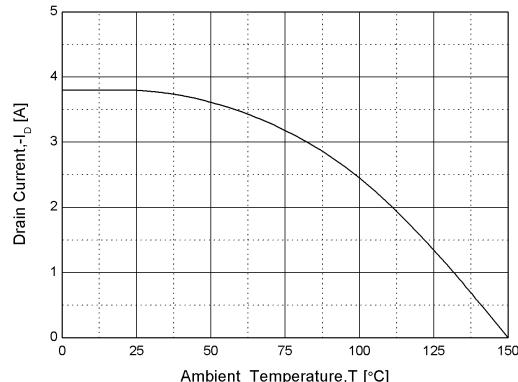


Figure10. Drain Current vs. Ambient Temperature

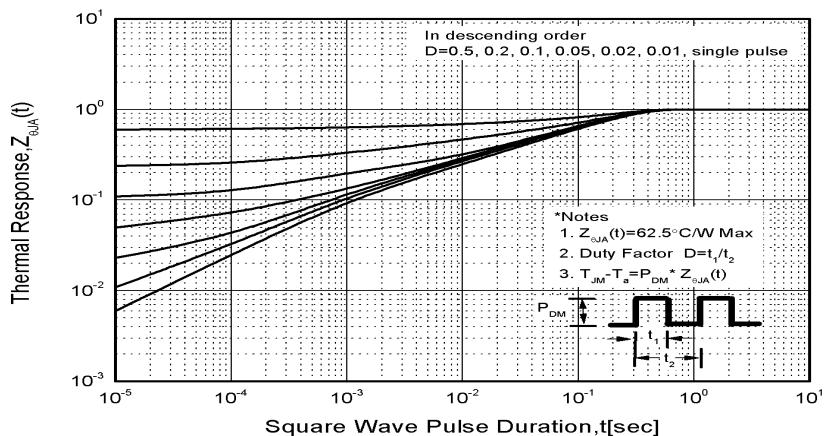
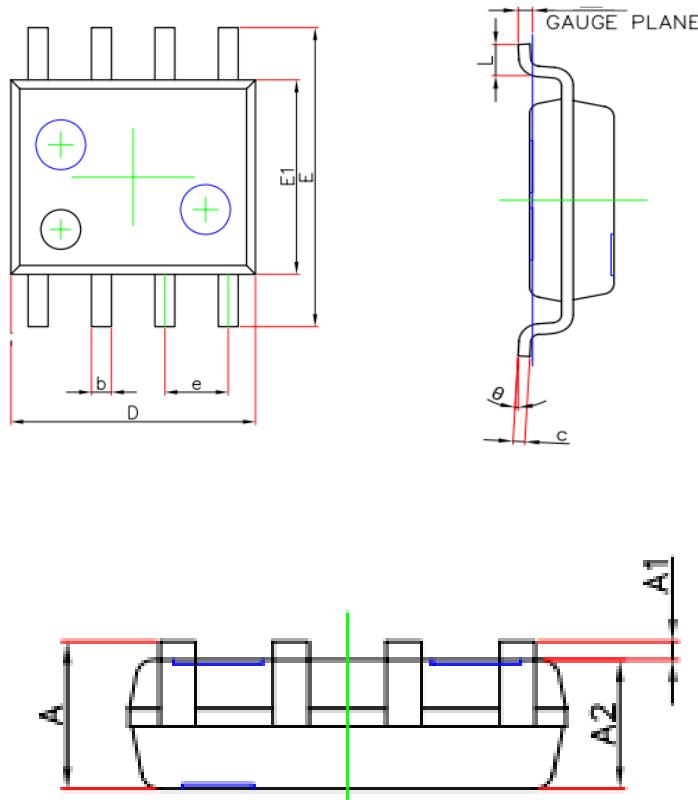


Figure11. Transient Thermal Response Curve

## SOP-8 PACKAGE OUTLINE DRAWING



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.063	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E1	3.800	4.000	0.150	0.157
E	5.800	6.200	0.228	0.244
e	1.27(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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